Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:	
Glass and metal	
Overall Length:	
1.250 inches	
End Application:	
Radar set, an/tpn-18a	
Mounting Facility Qua	ntity:
1	
Joint Electronic Devic	e Engineering Council/jedec/case Outline Designation:
D0-4	
Electrode Internally-el	ectrically Connected To Case:
Cathode	
Mounting Method:	
Threaded stud	
Features Provided:	
Hermetically sealed cas	e
Overall Width Across	Flats:
0.431 inches	
Thread Size:	
0.190 inches	
Semiconductor Materi	al:
Silicon	
Voltage Rating In Volts	S Per Characteristic:
400.0 working peak rev	erse voltage, peak total value
Current Rating Per Ch	aracteristic:
22.00 amperes source of	utoff current preset
Maximum Operating T	empurature Per Measurement Point:
150.0 degrees celsius c	ase
Test Data Document:	
24930-g390168 drawinç	g (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specificati	on, standard or other document that may be referenced in a basic governing drawing)
Thread Series Designa	itor:
Unf	
Terminal Type And Qu	antity:
1 tab, solder lug and 1	hreaded stud
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	